**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This triac is intended for use in motor control circuits where high blocking voltage, high static and dynamic dV/dt as well as high dlcom/dt can occur. This "series F0" triac will commutate the full rated RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150$  °C) without the aid of a snubber.

### 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- · High immunity to false turn-on by dV/dt
- · Isolated mounting base package
- High junction operating temperature capability  $(T_{j(max)} = 150 \text{ °C})$
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- · High voltage capability
- · Optimized for highest noise immunity

## 3. Applications

- Compressor starting control circuits
- · General purpose motor controls
- · Reversing induction motor controls e.g. vertical axis washing machines
- Applications subject to high temperature (T<sub>i(max)</sub> = 150 °C)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 106 ^{\circ}\text{C}$ ; $\overline{\text{Fig. 1}}$ ; $\overline{\text{Fig. 2}}$ ; $\overline{\text{Fig. 3}}$	-	-	8	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; $Fig. 4$ ; $Fig. 5$	-	-	60	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	-	65	Α
Tj	junction temperature		-	-	150	°C
Static chara						

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$		5	-	20	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	5	-	20	mA	
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$		5	-	20	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>		-	-	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>		-	1.3	1.65	V
Dynamic char	acteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit		500	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit; Fig. 12		6	-	-	A/ms

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2——T1
2	T2	main terminal 2		G sym051
3	G	gate		Symost
mb	n.c.	mounting base; isolated	1 2 3 TO-220F (SOT186A)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package								
	Name	Name Description							
BTA308X-800F0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A						
BTA308X-800F0/L03	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A						

# 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 106 \text{ °C}$ ; $Fig. 1$ ; $Fig. 2$ ; $Fig. 3$	-	8	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	60	Α
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	65	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	18	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 0.2 A	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

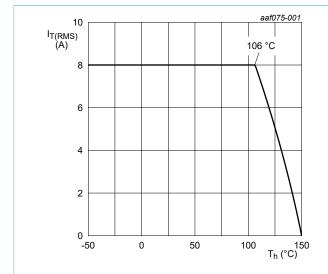


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

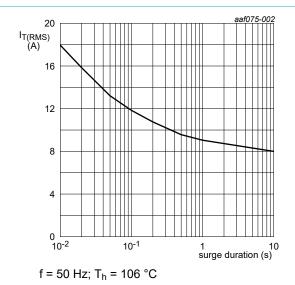


Fig. 2. RMS on-state current as a function of surge duration; maximum values

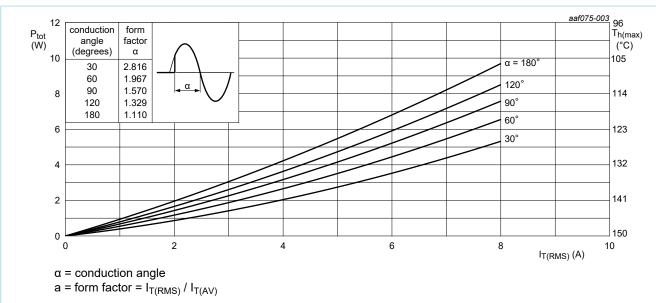


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

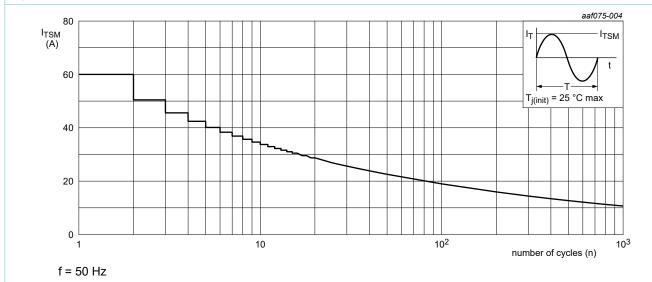
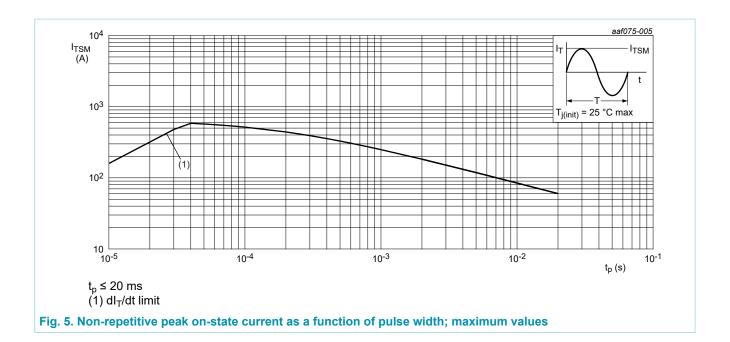


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4.5	K/W
	heatsink	full cycle or half cycle; without heatsink compound	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

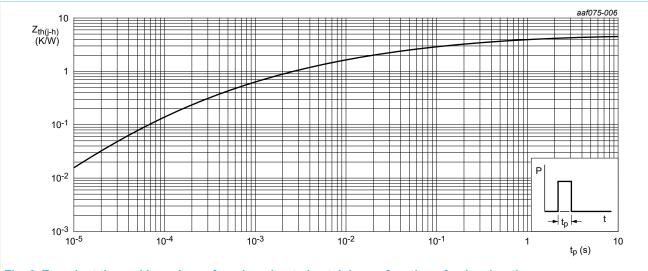


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

### 9. Isolation characteristics

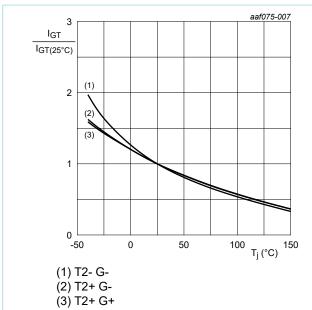
**Table 6. Isolation characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$	5	-	20	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	5	-	20	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	5	-	20	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	75	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	50	mA
Н	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 150 °C; Fig. 11	0.2	0.45	-	V
D	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	-	0.5	mA
Dynamic cl	naracteristics		·			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 20 V/µs; (snubberless condition); gate open circuit; Fig. 12	6	-	-	A/ms



junction temperature

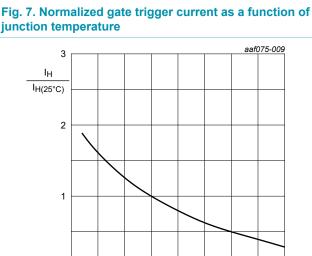


Fig. 9. Normalized holding current as a function of junction temperature

0

50

-50

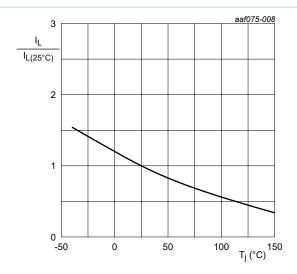
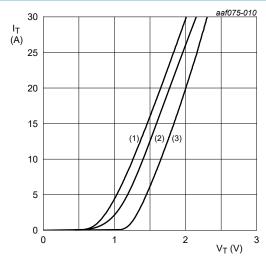


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.001 V;  $R_s$  = 0.0388 Ω (1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

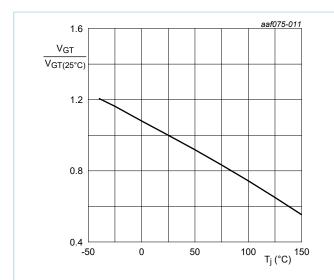


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

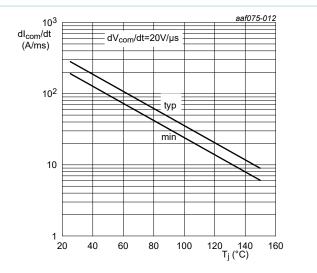
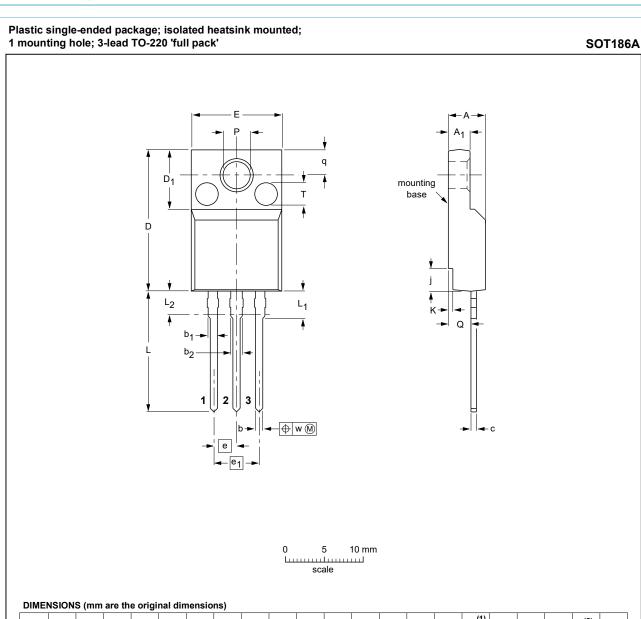


Fig. 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

# 11. Package outline



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	С	D	D <sub>1</sub>	E	е	e <sub>1</sub>	j	K	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	Р	Q	q	T <sup>(2)</sup>	w
mm	4.6 4.0	2.9	0.9	1.1 0.9	1.4 1.0	0.7	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2	2.6 2.3	3.0	2.5	0.4

#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are #  $2.5 \times 0.8$  max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F				<del>02-04-09</del> 06-02-14

Fig. 13. Package outline TO-220F (SOT186A)

# 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com
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Date of release: 24 March 2017

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OOO «ЛайфЭлектроникс" "LifeElectronics" LLC

ИНН 7805602321 КПП 780501001 P/C 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 3010181090000000703 БИК 044030703

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